

# CO<sub>2</sub> Reduction to Methanol on TiO<sub>2</sub>-Passivated GaP Photocatalysts

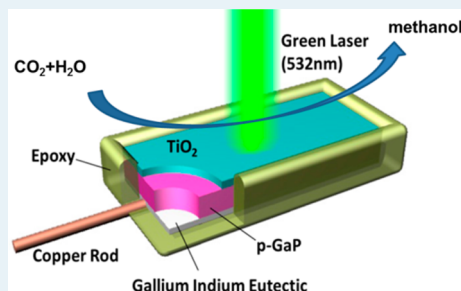
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**S** Supporting Information

**ABSTRACT:** In the past, the electrochemical instability of III–V semiconductors has severely limited their applicability in photocatalysis. As a result, a vast majority of the research on photocatalysis has been done on TiO<sub>2</sub>, which is chemically robust over a wide range of pH. However, TiO<sub>2</sub> has a wide band gap (3.2 eV) and can only absorb ~4% of the solar spectrum, and thus, it will never provide efficient solar energy conversion/storage on its own. Here, we report photocatalytic CO<sub>2</sub> reduction with water to produce methanol using TiO<sub>2</sub>-passivated GaP photocathodes under 532 nm wavelength illumination. The TiO<sub>2</sub> layer prevents corrosion of the GaP, as evidenced by atomic force microscopy and photoelectrochemical measurements. Here, the GaP surface is passivated using a thin film of TiO<sub>2</sub> deposited by atomic layer deposition (ALD), which provides a viable, stable photocatalyst without sacrificing photocatalytic efficiency. In addition to providing a stable photocatalytic surface, the TiO<sub>2</sub> passivation provides substantial enhancement in the photoconversion efficiency through passivation of surface states, which cause nonradiative carrier recombination. In addition to passivation effects, the TiO<sub>2</sub> deposited by ALD is n-type due to oxygen vacancies and forms a pn-junction with the underlying p-type GaP photocathode. This creates a built-in field that assists in the separation of photogenerated electron–hole pairs, further reducing recombination. This reduction in the surface recombination velocity (SRV) corresponds to a shift in the overpotential of almost 0.5 V. No enhancement is observed for TiO<sub>2</sub> thicknesses above 10 nm, due to the insulating nature of the TiO<sub>2</sub>, which eventually outweighs the benefits of passivation.

**KEYWORDS:** photoelectrochemical, GaP, CO<sub>2</sub> reduction, TiO<sub>2</sub> passivated, methanol



The photoelectrochemical reduction of CO<sub>2</sub> is an exciting reaction system with the ability to convert an abundant greenhouse gas to combustible hydrocarbon fuels using sunlight. The direct conversion of solar-to-chemical energy has several advantages over solar-to-electric energy conversion, most notably, the ability to store large amounts of energy (~GW) in chemical bonds that can later be released in a carbon neutral cycle.<sup>1</sup> Many attempts have been made to reduce CO<sub>2</sub> by 2e<sup>−</sup> to various species such as CO and formic acid, as reported in previous literature.<sup>2</sup> Few researchers have achieved further reduction to CH<sub>3</sub>OH or CH<sub>4</sub>.<sup>3</sup> Methanol is an attractive product with a relatively high energy density, which can be easily integrated into the existing liquid fuel technologies.<sup>1g,4</sup> However, the photocatalytic reduction of CO<sub>2</sub> with H<sub>2</sub>O to methanol requires six electrons and many intermediate species, some of which have extremely high energy barriers.<sup>5</sup> The most likely first step in this multielectron reaction is the one electron reduction to the CO<sub>2</sub><sup>−</sup> intermediate,<sup>6</sup> which lies 1.7 eV above the conduction band of TiO<sub>2</sub> and 1.2 eV above GaP. The mechanism for electrochemical CO<sub>2</sub> reduction was first proposed by Bockris et al.<sup>7</sup> The high overpotential required for this reaction was attributed to the formation of the CO<sub>2</sub><sup>−</sup> intermediate, which consequently converts to CO via the general process CO<sub>2</sub> + e<sup>−</sup> → CO<sub>2</sub><sup>−</sup>, CO<sub>2</sub><sup>−</sup> + 2H<sup>+</sup> + e<sup>−</sup> → CO + H<sub>2</sub>O.<sup>1c,i,3a,8</sup> In 1978, Hallman's group first reported CO<sub>2</sub> reduction on p-GaP under 365 nm illumination with an applied overpotential of −1.4 V (vs SCE).<sup>2a</sup> Fujishima and

Honda demonstrated photoelectrocatalytic reduction of CO<sub>2</sub> to formaldehyde and methanol by irradiating TiO<sub>2</sub> and GaP with the UV light at an overpotential of −1.5 V (vs SCE).<sup>2b,9</sup> Canfield later reported CO<sub>2</sub> reduction to methanol on p-InP with an overpotential of −1.3 V (vs SCE).<sup>2h</sup> More recently, Bocarsly's group demonstrated pyridinium-catalyzed CO<sub>2</sub> reduction on GaP photocathodes with overpotentials between −0.7 V and −0.2 V (vs SCE) under UV light.<sup>3a</sup> Despite these interesting prior results, the stability of these materials against photocorrosion has not been addressed.

In the work presented here, we investigate the photocatalytic performance and stability of TiO<sub>2</sub>-passivated p-GaP using atomic force microscopy (AFM), photoelectrochemistry, and optical microscopy. The photocatalytic efficiency is studied systematically as a function of TiO<sub>2</sub> layer thickness using a three-terminal potentiostat. The products are detected using NMR spectroscopy and gas chromatography, systematically as a function of applied overpotential.

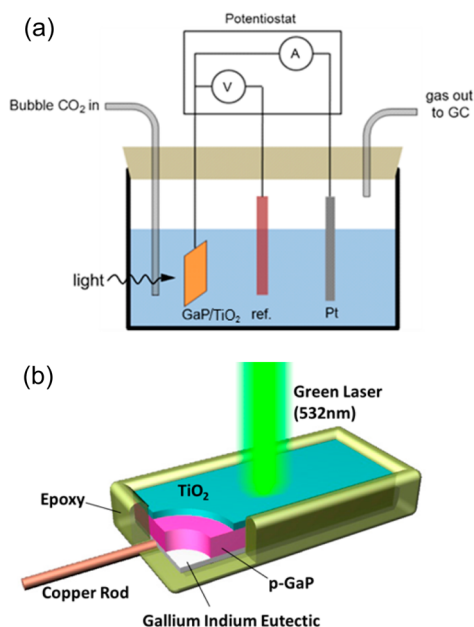
Zn doped p-type (100) oriented GaP with a dopant concentration of 2 × 10<sup>18</sup> cm<sup>−3</sup> was used as the photocatalyst for CO<sub>2</sub> reduction with an active area of 0.5 cm × 1 cm. Atomic layer deposition (ALD) of anatase TiO<sub>2</sub> was performed at 250 °C on the p-GaP wafers with TiCl<sub>4</sub> as the titanium source and

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75 water vapor as the oxygen source. The antase crystal phase was  
 76 verified by Raman spectroscopy. Using ellipsometry, we  
 77 established that 100 cycles of ALD produces a 4 nm thick  
 78  $\text{TiO}_2$  film and 1000 cycles produces a 40 nm film. A Ga–In  
 79 eutectic film was painted on the back of the p-GaP to form an  
 80 Ohmic contact. The Ga–In contact was then connected to the  
 81 external circuitry with a copper wire and coated with epoxy  
 82 cement to insulate it from the electrolytic solution, as illustrated  
 83 in Figure 1b. Although this planar geometry is not ideal for high



**Figure 1.** Schematic diagram of (a) photoelectrochemical measurement setup and (b) sample geometry of the  $\text{TiO}_2$ -passivated p-GaP photocathode.

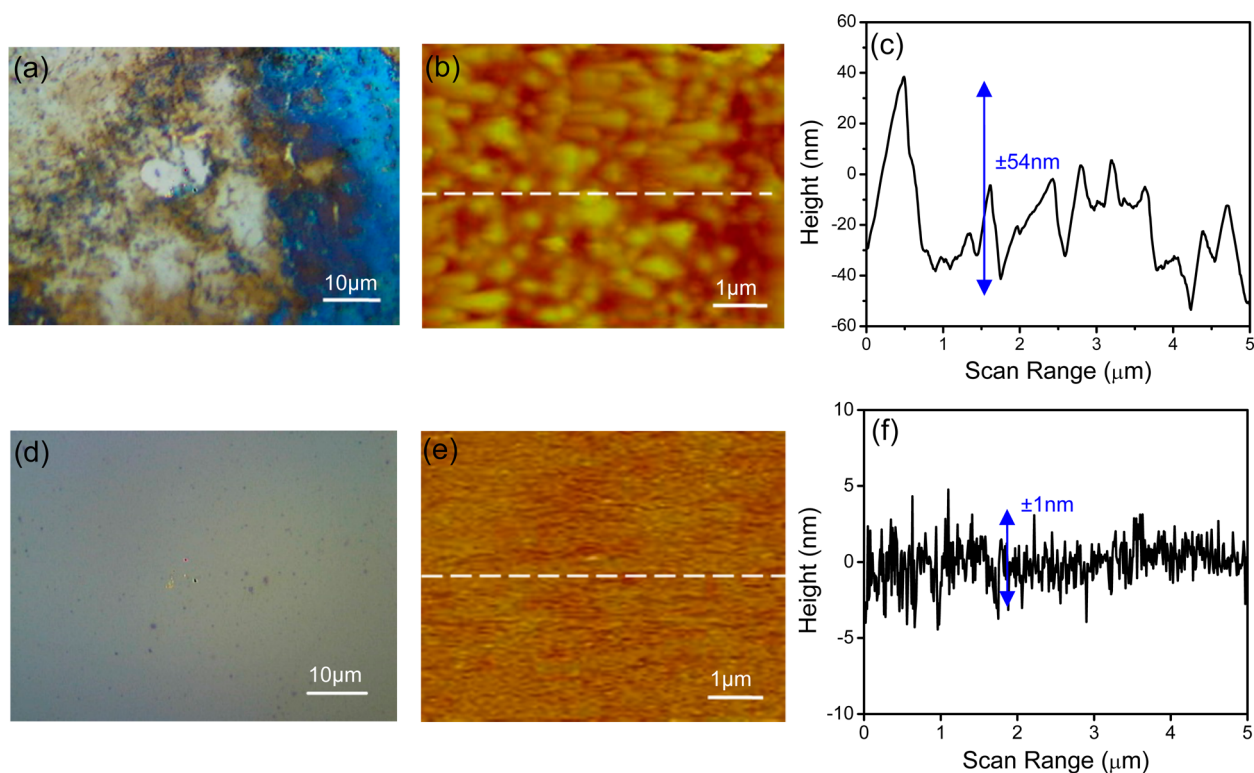
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84 efficiency photoconversion, it enables us to study surface  
 85 stability. A three-terminal potentiostat was used with the  
 86 prepared semiconductor samples as the working electrode, a  
 87 Ag/AgCl electrode as the reference electrode, and a Pt  
 88 electrode functioning as a counter electrode, as shown in  
 89 Figure 1a. The photocatalytic reaction rates of two sets of  
 90 samples were measured in a 2 mL solution of 0.5 M NaCl, with  
 91 and without 10 mM pyridine, while continuously bubbling  $\text{CO}_2$   
 92 through the solution. NaCl (0.5 M) was chosen as the  
 93 electrolyte solution because of its high conductance and its  
 94 ability to stabilize the intermediate states involved in the  $\text{CO}_2$   
 95 reduction.<sup>10</sup> In this setup, we analyze the products evolving at  
 96 the working electrode, instead of at the counter electrode. It is  
 97 likely that oxygen is also produced in the reaction.

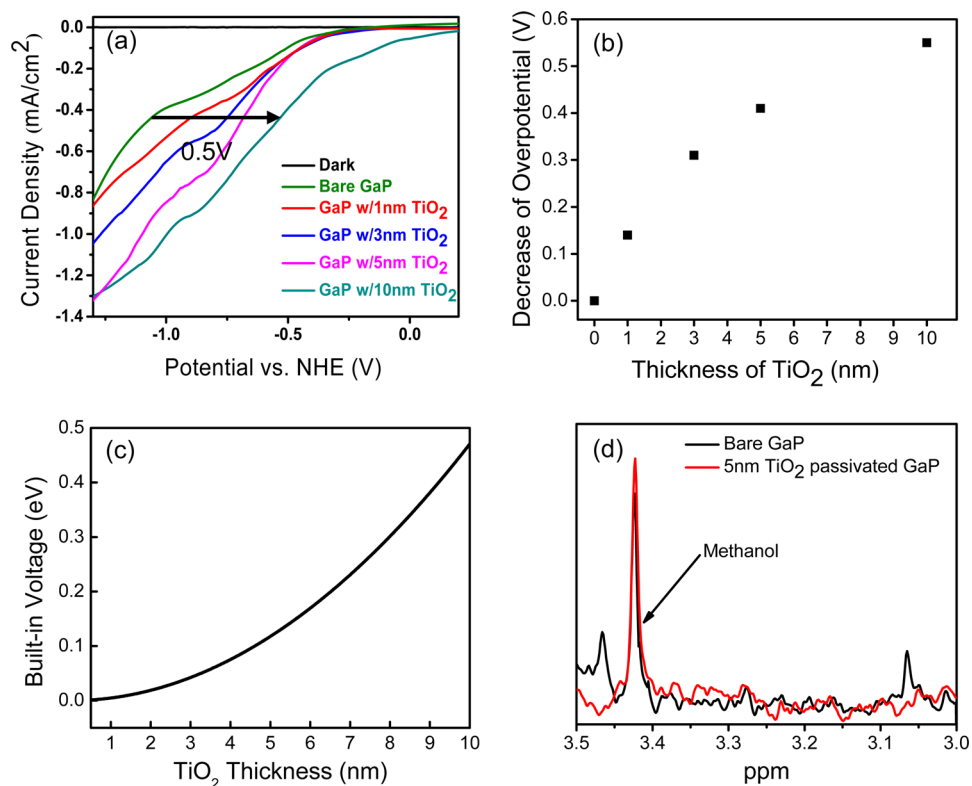
98 While photocatalysis on GaP (and other III–V compound  
 99 semiconductors) has been demonstrated previously,<sup>2h,3a,11</sup> this  
 100 material corrodes rapidly under photoelectrochemical con-  
 101 ditions and is significantly degraded after just 30 min of  
 102 illumination. In order to make GaP photochemically stable, we  
 103 passivated the surface using a thin film of  $\text{TiO}_2$  deposited by  
 104 ALD, as illustrated schematically in Figure 1b. Figure 2a,b show  
 105 optical microscope and atomic force microscope images of the  
 106 bare GaP surface after 8 h of illumination. Figure 2c shows a  
 107 plot of the surface topography obtained along the dashed white  
 108 line in Figure 2b, showing an RMS roughness of  $\pm 54$  nm,  
 109 which indicates that substantial photocorrosion has taken place  
 110 and that this will not serve as a viable photocatalyst. In contrast,

the photocurrent density of  $\text{TiO}_2$ -passivated GaP is stable for 8  
 h. The optical microscope image (Figure 2d) and atomic force  
 microscope image (Figure 2e) exhibit no evidence of surface  
 corrosion or damage after 8 h, with an RMS roughness of  $\pm 1$   
 nm (Figure 2f), indicating that this is a long-term, stable  
 photocatalyst. Here, the  $\text{TiO}_2$  significantly improves the  
 photostability of the GaP surface, however, more extensive  
 time-dependent studies are needed in order to establish the  
 extent of this long-term stability.

In addition to providing a stable photocatalytic surface, the  
 $\text{TiO}_2$  passivation layer results in an increase in the photo-  
 conversion efficiency. Figure 3a shows the photocurrent–  
 voltage curves for GaP passivated with various thicknesses of  
 $\text{TiO}_2$  measured in a 0.5 M NaCl, 10 mM pyridine solution  
 under 532 nm illumination. During these measurements,  $\text{CO}_2$   
 is continuously bubbled through the solution. Bare GaP (green  
 curve) has an onset of photocurrent at a potential of  
 approximately  $-0.15$  V (vs NHE). For  $\text{TiO}_2$ -passivated GaP,  
 we see a clear shift in the overpotential required to drive this  
 reaction with increasing thickness of the  $\text{TiO}_2$ , as plotted in  
 Figure 3b. Table 1 lists the shift of onset overpotential of  
 samples with different thicknesses of  $\text{TiO}_2$ . For example, the  
 onset potential for 10 nm  $\text{TiO}_2$  (red curve) is shifted by 0.5 V  
 with respect to bare GaP. This shift is attributed to the  
 passivation of surface states that cause nonradiative recombi-  
 nation and the formation of a pn-junction, which is created  
 because the ALD-deposited  $\text{TiO}_2$  tends to be n-type doped due  
 to oxygen vacancies.<sup>12</sup> Figure 3c shows the built-in potential for  
 the junction calculated using  $V_{bi} = ((W_D^2 q)/(2 \epsilon_0 \epsilon_a \epsilon_d)) (N_a$   
 $N_d(N_a \epsilon_a + N_d \epsilon_d)/(N_a + N_d)^2)$ , assuming a doping  
 concentration of  $N_a = 5 \times 10^{18} \text{ cm}^{-3}$ .<sup>13</sup> Here,  $W_D$  is the  
 depletion width of the GaP– $\text{TiO}_2$  junction, which is a function  
 of the  $\text{TiO}_2$  layer thickness. This simple calculation predicts  
 values similar to the experimentally observed shift in the  
 overpotential plotted in Figure 3b. Beyond 10 nm, however, the  
 photocurrent decreases rapidly with increasing  $\text{TiO}_2$  thickness  
 due to band bending at the n-type  $\text{TiO}_2$ /electrolyte interface,  
 which blocks electrons. No enhancement is observed for  $\text{TiO}_2$   
 thicknesses above 10 nm, due to the insulating nature of the  
 $\text{TiO}_2$ , which eventually outweighs the benefits of passivation.  
 Although  $\text{TiO}_2$  does not absorb light at 532 nm, the pn-  
 junction formed with the GaP enables separation of the  
 photogenerated charge in the actively absorbing GaP. Figure 3d  
 shows the NMR spectra taken after 8 h of illumination with an  
 overpotential of  $-0.50$  V vs NHE for GaP with and without  
 $\text{TiO}_2$  passivation. These data show a clear peak corresponding  
 to methanol, as reported previously by Barton et al.<sup>3a</sup> Gas  
 chromatography FID data have also been used to verify the  
 production of methanol, as shown in Supporting Information  
 Figure S1. On the basis of these GC FID data for the 5 nm  
 thick  $\text{TiO}_2$  sample, we calculated that  $4.9 (\pm 0.02) \mu\text{mol}$  of  
 $\text{CH}_3\text{OH}$  are produced during an 8 h reaction consuming 5.2  
 Coulombs of charge. Dividing by this ratio by the  
 stoichiometric factor of 6, yields a Faradaic efficiency of 55%.  
 Also, according to the GC TCD data of the same experiment,  
 $\text{H}_2$  is produced with a Faradaic efficiency of 30%. The  
 photoconversion efficiency, however, can be significantly less  
 than this due to nonradiative recombination, which is unknown,  
 particularly for this planar sample geometry. As a control  
 experiment, the same reaction was run under the same  
 electrochemical conditions of  $-0.50$  V vs NHE without laser  
 illumination, which resulted in no measurable current and no  
 detectable methanol in the NMR spectra. In order to rule out



**Figure 2.** (a) Optical microscope image, (b) atomic force microscope image, and (c) surface topography of bare GaP surface after an 8 h reaction at  $-0.5$  V overpotential. (d) Optical microscope image, (e) atomic force microscope image, and (f) surface topography of 5 nm TiO<sub>2</sub> on GaP surface after an 8 h reaction.



**Figure 3.** (a) Photocatalytic current–potential curves of GaP photocatalysts with different TiO<sub>2</sub> thicknesses in a 0.5 M NaCl, 10 mM pyridine solution under 532 nm wavelength laser illumination. (b) Decrease of overpotential plotted as a function of TiO<sub>2</sub> thickness on GaP. (c) Calculated built-in voltage plotted as a function of TiO<sub>2</sub> thickness. (d) NMR spectra showing methanol production using bare GaP and 5 nm TiO<sub>2</sub>-passivated GaP photocatalysts at an overpotential of  $-0.50$  V.



**Table 1. Shift of Onset Overpotential for Samples with Different Thicknesses of TiO<sub>2</sub>**

catalysts	shift of onset overpotential compared to bare GaP (V)
bare GaP	0
1 nm TiO <sub>2</sub> @GaP	0.13
3 nm TiO <sub>2</sub> @GaP	0.31
5 nm TiO <sub>2</sub> @GaP	0.40
10 nm TiO <sub>2</sub> @GaP	0.52

other sources of carbon in this reaction, we used isotopically labeled <sup>13</sup>CO<sub>2</sub> as the carbon source in this reaction and observed <sup>13</sup>CH<sub>3</sub>OH in the <sup>13</sup>C NMR spectrum shown in Supporting Information Figure S5.<sup>14</sup> In addition, we repeated the experiment, purging with Ar instead of CO<sub>2</sub>, and found no production of hydrocarbons. Therefore, we are confident that CO<sub>2</sub> is the only carbon source in this reaction. Previously, it was reported that a pyridine catalyst is required to drive this reaction on GaP. The pyridinium radical serves as a one-electron charge-transfer mediator, which is capable of efficiently transferring all six electrons to reduce CO<sub>2</sub> to methanol, thereby circumventing the high energy barrier of the one-electron reduction of CO<sub>2</sub> mentioned above.<sup>11</sup> However, we observe the same methanol peak in our NMR spectra without pyridine in solution (see Supporting Information Figure S2), indicating that this catalyst is not, in fact, required to drive this reaction at low overpotentials. Although CH<sub>3</sub>OH products are observed without pyridine, the yield is one-third that of the system with pyridine, indicating that the pyridine, in fact, helps lower the energy barriers of the reaction by forming an inner-sphere-type electron-transfer system.<sup>11,15</sup> Atomic force microscopy shows that the GaP/TiO<sub>2</sub> is photochemically stable without pyridine, as shown in Supporting Information Figure S3.

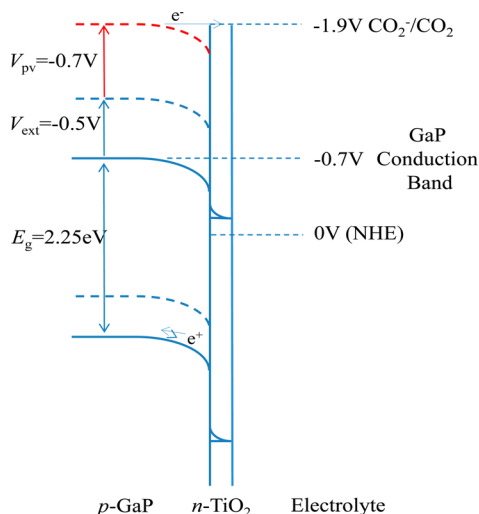
In order to understand the mechanism of this reaction, we must consider the energetics of the electrons in this photocatalytic structure. The conduction bands of GaP and TiO<sub>2</sub> lie slightly above NHE at −0.7 V and −0.2 V versus NHE, respectively, as plotted in Figure 4. This leaves an energy barrier of at least 1.2 V for the electrons to overcome in the reduction of CO<sub>2</sub>. The −0.5 V externally applied overpotential

( $V_{\text{ext}}$ ) accounts for part of this required energy, and the photovoltage produced at the internal pn-junction and/or the liquid-semiconductor junction ( $V_{\text{pv}}$ ) can easily account for the remaining −0.7 V, as depicted in Figure 4. From the flat-band voltage, we can obtain the open circuit voltage, as follows:  $(V_{\text{oc}})_{\text{max}} = |V_{\text{fb}} - V_{\text{redox}}|$ , where  $V_{\text{fb}}$  is flat-band potential and  $V_{\text{redox}}$  is the potential of the redox couple.<sup>16</sup> From Mott–Schottky measurements, we obtained a flat-band potential of 0.4 V versus NHE, which is consistent with previous values from literature.<sup>3a,17</sup> Using  $V_{\text{redox}}$  (ferricyanide/ferrocyanide) = 0.36 V, we obtain an open circuit voltage of  $V_{\text{oc}} = 0.76$  V, which is large enough to cover the remaining −0.7 V depicted in Figure 4. This photovoltage is reasonable considering GaP's relatively large band gap of 2.25 eV.

These estimations assume that the electrons traverse the TiO<sub>2</sub> layer ballistically and do not equilibrate to the TiO<sub>2</sub> conduction band edge. In the diffusive case, an additional 0.5 V would be required. We believe this is one of the reasons why the TiO<sub>2</sub> layer must be made very thin. Several aspects of these results and their underlying mechanism are quite surprising. First, we had initially thought that the TiO<sub>2</sub> layer, which is insulating and has a low conduction band energy, would lower the overall photocatalytic efficiency (i.e., photocurrent), but would, at least, provide a stable, viable catalyst. Much to our surprise, the TiO<sub>2</sub> layer actually improved the overall photoconversion efficiency. The reasons for this are 3-fold: (1) The TiO<sub>2</sub> reduces nonradiative recombination of the photoexcited electron–hole pairs. (2) The electrons traverse the TiO<sub>2</sub> ballistically and, therefore, do not relax to the conduction band edge. (3) The formation of a pn-junction provides an additional photovoltage required to drive the reaction.

It is important to note, however, that the CO<sub>2</sub><sup>•−</sup> reduction potential of −1.9 V versus NHE is calculated from simple thermodynamic considerations for isolated CO<sub>2</sub><sup>•−</sup> species, and does not include the effects of the solution or catalytic surface. As a result, the energetics of the actual CO<sub>2</sub><sup>•−</sup> intermediates can be quite different due to the presence of the aqueous solution and/or the catalytic surface. In a mechanism proposed by Anpo et al., the CO<sub>2</sub><sup>•−</sup> intermediate is strongly bound to a proposed Ti<sup>3+</sup> active site (oxygen vacancy) on the TiO<sub>2</sub> surface, thus lowering its energy.<sup>18</sup> Another strategy for lowering the reaction barrier is stabilizing the CO<sub>2</sub><sup>•−</sup> intermediate, which was recently demonstrated using an ionic liquid electrolyte cocatalyst where the cation forms a complex with the anionic intermediate.<sup>19</sup> Two-electron processes have also been proposed by Tanaka et al., which would circumvent this first intermediate step altogether.<sup>20</sup> Although several mechanisms have been proposed in the literature, further spectroscopic studies are needed in order to verify the catalytic reaction pathway.

In conclusion, we report photocatalytic CO<sub>2</sub> reduction on TiO<sub>2</sub>-passivated GaP. The TiO<sub>2</sub> passivation layer successfully stabilizes the GaP surface in solution, preventing it from photocorrosion. In addition, the TiO<sub>2</sub> passivation layer provides enhancement in the photoconversion efficiency through the passivation of surface states and the formation of a charge separating pn-region, which reduces carrier recombination and lowers the overpotential required to initiate this reaction by approximately 0.5 V. This general approach of passivating narrower band gap semiconductors with TiO<sub>2</sub> will enable more efficient photocatalysts to be developed and a broad range of materials to be considered for photocatalysis

**Figure 4.** Energy band alignment of GaP and TiO<sub>2</sub> together with the relevant redox potentials of CO<sub>2</sub>.

that make more efficient use of the solar spectrum. We also observe CH<sub>3</sub>OH evolution with and without pyridine catalyst, indicating that this catalysts is not, in fact, required to drive this reaction at low overpotentials.

## ASSOCIATED CONTENT

### Supporting Information

Gas chromatography data; <sup>1</sup>H NMR spectra of methanol; images using optical microscopy, atomic force microscopy, and surface topography, CH<sub>3</sub>OH production plotted as a function of time; and <sup>13</sup>C NMR spectrum of methanol. This material is available free of charge via the Internet at <http://pubs.acs.org>.

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### Notes

The authors declare no competing financial interest.

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